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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Makoto SASAKI

Serial No.: 09/532,892

Group Art Unit: 2815

Filed: March 22, 2000

Examiner: P. Brock, II

For: SEMICONDUCTOR DEVICE WITH COPPER FUSE SECTION

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

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EXCESS CLAIM FEE PAYMENT LETTER

Sir:

Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below.

The Commissioner is authorized to charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

	<u>AFTER AMENDMENT</u>	<u>PREV. PAID FOR</u>	<u>EXTRA CLAIMS PRESENT</u>	<u>RATE</u>	<u>FEE DUE</u>
Total Claims	19	20	= 0	x \$18.00	\$ 0.00
Indep. Claims	4	3	= 1	x \$84.00	\$84.00

TOTAL ADDITIONAL FEE FOR THIS AMENDMENT

\$84.00

A check in the amount of \$84.00 is enclosed to cover the excess claim fees. A duplicate copy of this sheet is enclosed.

Respectfully Submitted,

Date: 9/5/02

Peter A. Balnave

Peter A. Balnave

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AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated June 7, 2002, please amend the above-identified application as follows:

IN THE CLAIMS: ✓

Please cancel claims 6 and 25 without prejudice or disclaimer.

Please amend claims 1, 4, 5, 17, 20 and 23 as follows:

- C1 SUB D1
1. (Thrice Amended) A semiconductor memory device, including a copper fuse section that is oxidized by a laser beam in an oxidizing environment, comprising:
- a dielectric film including a first film section formed on a substrate, a second film section formed on said first film section, and a third film section formed over said second film section;
 - a wiring line structure, including:
 - a first and a second wiring line, each of said first and second wiring lines formed directly upon said second film section of said dielectric film without an intervening film therebetween and extending in an opposite direction, and
 - said copper fuse section formed on said first film section of said dielectric film, an end of said copper fuse section being directly connected to said first wiring line by a first section of said first wiring line, which penetrates a portion of said second film section, and another end of said copper fuse section being directly connected to said second